

TRANSMITTAL OF INFORMATION DISCLOSURE STATEMENT
(Under 37 CFR 1.97(b) or 1.97(c))

Docket No.
BUR920020109US1

In Re Application Of **Burnham et al**

1000 River Road
Essex Junction, VT 05452

Serial No
10/604,905

Filing Date
08/26/2003

Examiner

Group Art Unit
2912

Title: **METHOD FOR FABRICATING A NITRIDED SILICON-OXIDE GATE DIELECTRIC**

Address to:

**Assistant Commissioner for Patents
Washington, D.C. 20231**

37 CFR 1.97(b)

1. ☒ The Information Disclosure Statement submitted herewith is being filed within three months of the filing of a national application other than a continued prosecution application under 37 CFR 1.53(d); within three months of the date of entry of the national stage as set forth in 37 CFR 1.491 in an international application; before the mailing of a first Office Action on the merits, or before the mailing of a first Office Action after the filing of a request for continued examination under 37 CFR 1.114.

37 CFR 1.97(c)

2. ☐ The Information Disclosure Statement submitted herewith is being filed after the period specified in 37 CFR 1.97(b), provided that the Information Disclosure Statement is filed before the mailing date of a Final Action under 37 CFR 1.113, a Notice of Allowance under 37 CFR 1.311, or an Action that otherwise closes prosecution in the application, and is accompanied by one of:
- ☐ the statement specified in 37 CFR 1.97(e);
- OR**
- ☐ the fee set forth in 37 CFR 1.17(p).

TRANSMITTAL OF INFORMATION DISCLOSURE STATEMENT

(Under 37 CFR 1.97(b) or 1.97(c))

Docket No.
BUR920020109US1In Re Application: **Burnham et al**1000 River Road
Essex Junction, VT 05452Serial No.
10/604,905Filing Date
08/26/2003

Examiner

Group Art Unit
2912**METHOD FOR FABRICATING A NITRIDED SILICON-OXIDE GATE DIELECTRIC****Payment of Fee**

(Only complete if Applicant elects to pay the fee set forth in 37 CFR 1.17(p))

- ☐ A check in the amount of _____ is attached.
- ☒ The Assistant Commissioner is hereby authorized to charge and credit Deposit Account No. **09-0456** as described below. A duplicate copy of this sheet is enclosed.
- ☐ Charge the amount of _____
- ☐ Credit any overpayment.
- ☒ Charge any additional fee required.

Certificate of Transmission by Facsimile*

I certify that this document and authorization to charge deposit account is being facsimile transmitted to the United States Patent and Trademark Office (F

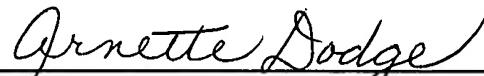
(Date)

Signature

Typed or Printed Name of Person Signing Certificate

Certificate of Mailing by First Class Mail

I certify that this document and fee is being deposited February 16, 2004 with the U.S. Postal Service as first class mail under 37 C.F.R. 1.8 and is addressed to the Assistant Commissioner for Patents, Washington, D.C. 20231.



Signature of Person Mailing Correspondence

Arnette Dodge

Typed or Printed Name of Person Mailing Certificate

***This certificate may only be used if paying by deposit account.**

Signature

William D. Sabo, Esq., Reg. No. 27,465Dated: **2/16/04**

CC:



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Docket: BUR920020109US1

Filing Date: 08/26/03
Application No.: 10/604905
Applicant: Burnham et al.

Examiner: Unassigned
Group Art Unit: Unassigned
Confirmation No.: _____

Title: METHOD FOR FABRICATING A NITRIDED SILICON-OXIDE GATE DIELECTRIC.

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT
UNDER 37 CFR 1.56, 1.97, 1.98

Honorable Commissioner of Patents and Trademarks
Washington, D. C. 20231

Sir:

Applicants submit herewith form PTO-1449, listing patents, publications, or other information of which they are aware which they believe may be material to patentability pursuant to 37 CFR 1.56(b), and in respect of which there may be a duty to disclose under 37 CFR 1.56(a), together with legible copies of the patents, publications, or other information listed.

While the items submitted with this Information Disclosure Statement may be material to patentability pursuant to 37 CFR 1.56, in accordance with 37 CFR 1.97(h) it shall not be construed to be an admission that any patent, publication, or other information cited is "prior art" or is material to patentability for this invention unless specifically designated as such. In accordance with 37 CFR 1.97(g), the filing of this Information Disclosure Statement shall not be construed to mean that a search has been made or that no other information material to patentability, as defined in 37 CFR 1.56(b), exists.

This Information Disclosure Statement is being filed with the filing of this application. Accordingly, it is not believed that any fee is required relating to the filing of this Information Disclosure Statement. If this is not the case, the Patent Office is hereby authorized to charge any related fee to Deposit Account No. 09-0456.

Date: 2/16/04

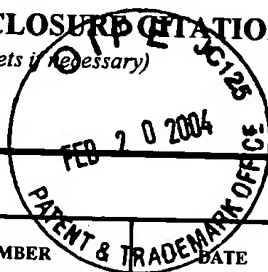
Respectfully submitted,

By: [Signature]

William D Sabe, Esq.
Registration No. 27,465
IBM Corporation - Zip 972E
1000 River Street
Essex Jct., VT 05452

INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)



Docket Number (Optional)

BUR920020109US1

Application Number

10/604905

Applicant(s)

Burnham et al.

Filing Date

08/26/03

Group Art Unit

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE

FOREIGN PATENT DOCUMENTS

REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

IBM Technical Disclosure Bulletin, Vol. 28, No. 6, November 1985, CONTROLLED NITRIDATION OF SiO₂ FOR THE FORMATION OF GATE INSULATORS IN FET DEVICES, Merz et al., Pages 2665-2666.

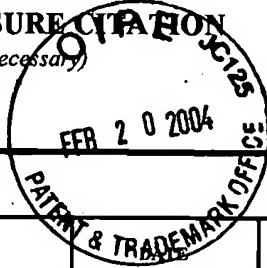
IBM Technical Disclosure Bulletin, Vol. 19, No. 4, September 1976, MNOS REACTOR PROCESS, Haggett et al., Page 1160.

EXAMINER

DATE CONSIDERED

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

INFORMATION DISCLOSURE CITATION
(Use several sheets if necessary)



Docket Number (Optional) BUR920020109US1		Application Number 10/604905
Applicant(s) Burnham et al.		
Filing Date 08/26/03	Group Art Unit	

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE

FOREIGN PATENT DOCUMENTS

	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
							YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

		IBM Technical Disclosure Bulletin, Vol. 14, No. 4, September 1971, TRANSCONDUCTANCE IN SILICON GATE NITRIDE-OXIDE IGFET, Dockerty et al., 1 sheet.

EXAMINER	DATE CONSIDERED
----------	-----------------

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.